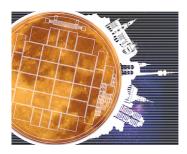
## 13th "Trento" Workshop on Advanced Silicon Radiation Detectors



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## Two Photon Absorption-TCT of irradiated LGADs

Low Gain Avalanche Diodes (LGAD) with different implantation dose and irradiated with 24 GeV/c protons at CERN-PS up to a fluence of 1e14 1 MeV neutron equivalent will be presented. The results of these measurements support the interpretation of a double junction effect as the primary responsible for the reduction of gain observed in these devices. The shape and magnitude of electric field was calculated profiting from the point-like spatial resolution of this technique. This method was also applied to PIN diodes of different runs.

**Primary authors:** PALOMO PINTO, Francisco Rogelio (Universidad de Sevilla (ES)); FERNANDEZ GARCIA, Marcos (Universidad de Cantabria (ES)); MOLL, Michael (CERN); VILA ALVAREZ, Ivan (Instituto de Física de Cantabria (CSIC-UC)); MONTERO, Raul (UPV/EHU)

Presenter: FERNANDEZ GARCIA, Marcos (Universidad de Cantabria (ES))